



1N483B thru 1N486B and 1N5194 thru 1N5196

SANTA ANA, CA For more information call: (714) 979-8220

FEATURES

- Voidless hermetically sealed glass package (00-35).
- Triple layer passivation.
- Metallurgically bonded.
- TX types available per MIL-S-19500/118C.
- 1N5194 thru 1N5196 only available in surface mount.

MAXIMUM RATINGS

Operating Temperature: -65°C to +200°C. Storage Temperature: -65°C to +200°C. Surge Current: 2A

ELECTRICAL CHARACTERISTICS

ТҮРЕ	WORIONG PEAK Reverse Voltage Vrwm	BREAKDOWN VOLTAGE (MIN.) V(BR)⊕100 µA	AVERAGE RECTIFIED CURRENT		FORWARD VOLTAGE DROP (MAX.) VF	CURI (MA	ERSE Rent XX.) Vrww	SURGE CURRENT (MAX.) (NOTE 1) Ic surge	JUNCTION Capacitance C & OV	
	VOLTS	VOLTS	AN	IPS	VOLTS	μA		AMPS	pF	
			25°C	150°C		25°C	150°C			
JAN 1N483B	70	80	.2	.05	1.0V (pk)	.025	5	2	8	
JAN 1N485B	180	200	.2	.05	@	.025	5	2	8	
JAN 1N486B	225	250	.2	.05	100mA pulse	.025	5	2	8	
JAN 1N5194 JAN 1N5195 JAN 1N5196		SAME AS JAN 1N485B SAME AS JAN 1N485B SAME AS JAN 1N486B								

PACKAGE: D07 for JAN 1N483B, 485B, 486B. D035 for JAN 1N5194, JAN 1N5195, and JAN 1N5196.

NOTE 1: $I_0 = 200 \text{ mAdc}$, 10 - 8.3 msec surges

MECHANICAL CHARACTERISTICS

Case: Hermetically sealed glass case. Lead Material: Tinned copper. Marking: Body painted, alpha numeric. Polarity: Cathode band.

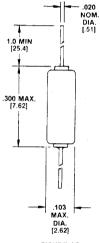


FIGURE 1A PACKAGE D07

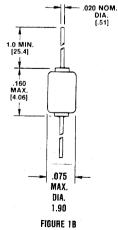


FIGURE 18 PACKAGE DO-35

GENERAL PURPOSE SILICON DIODES

1N483B - 1N486B. 1N5194 - 1N5196

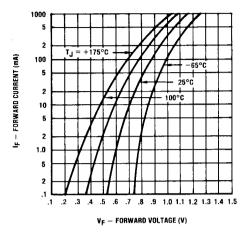


FIGURE 2 Forward Voltage VS. Forward Current

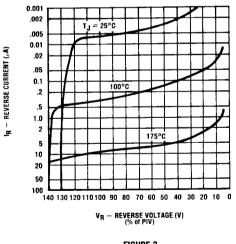


FIGURE 3 REVERSE VOLTAGE vs. REVERSE CURRENT

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